# Quad D Flip-Flop with Common Clock and Reset

# **High-Performance Silicon-Gate CMOS**

The MC74HC175A is identical in pinout to the LS175. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of four D flip-flops with common Reset and Clock inputs, and separate D inputs. Reset (active-low) is asynchronous and occurs when a low level is applied to the Reset input. Information at a D input is transferred to the corresponding Q output on the next positive going edge of the Clock input.

#### **Features**

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity 166 FETs or 41.5 Equivalent Gates
- Pb-Free Packages are Available\*



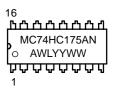
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#### MARKING DIAGRAMS

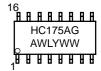


PDIP-16 N SUFFIX CASE 648





SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F





SOEIAJ-16 F SUFFIX CASE 966



A = Assembly Location

L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G = Pb-Free Package
= Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

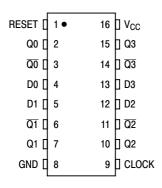


Figure 1. Pin Assignment

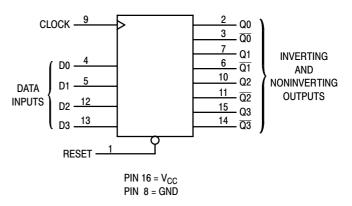
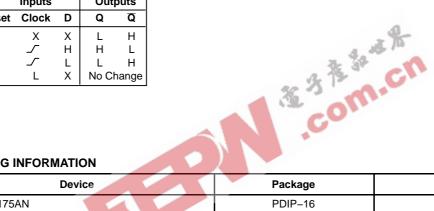


Figure 2. Logic Diagram

### **FUNCTION TABLE**

Inputs			Outputs	
Reset	Clock	D	Q	Q
L	Х	Χ	L	Н
н	_	Н	Н	L
Н	_	L	L	Н
Н	L	Χ	No Cł	nange



#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HC175AN	PDIP-16	500 Units / Rail
MC74HC175AD	SOIC-16	48 Units / Rail
MC74HC175ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC175ADR2	SOIC-16	2500 Units / Reel
MC74HC175ADR2G	SOIC-16 (Pb-Free)	2500 Units / Reel
MC74HC175ADTR2	TSSOP-16*	2500 Units / Reel
MC74HC175ADTR2G	TSSOP-16*	2500 Units / Reel
MC74HC175AFEL	SOEIAJ-16	2000 Units / Reel
MC74HC175AFELG	SOEIAJ-16 (Pb-Free)	2000 Units / Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. \*This package is inherently Pb–Free.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
I <sub>in</sub>	DC Input Current, per Pin	± 20	mA
I <sub>out</sub>	DC Output Current, per Pin	± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 50	mA
P <sub>D</sub>	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>in</sub> and Vout should be constrained to the range GND  $\leq$  (V<sub>in</sub> or V<sub>out</sub>)  $\leq$  V<sub>CC</sub>.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

 Plastic DIP: – 10 mW/°C from 65° to 125°C †Derating

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: – 6.1 mW/°C from 65° to 125°C
For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $ \begin{array}{c} \text{V}_{\text{CC}} = 2.0 \text{ V} \\ \text{(Figure 1)} \\ \text{V}_{\text{CC}} = 3.0 \text{ V} \\ \text{V}_{\text{CC}} = 4.5 \text{ V} \\ \text{V}_{\text{CC}} = 6.0 \text{ V} \\ \end{array} $	0 0 0	1000 600 500 400	ns

# DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	>
V <sub>IL</sub>	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	<
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\begin{split} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} &   I_{\text{out}}  \leq 2.4 \text{ mA} \\  I_{\text{out}}  \leq 4.0 \text{ mA} \\  I_{\text{out}}  \leq 5.2 \text{ mA} \end{split}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	

# DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V <sub>CC</sub>	– 55 to 25°C	≤ <b>85</b> ° <b>C</b>	≤ 125°C	Unit
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} \qquad  I_{\text{out}}  \le 2.4 \text{ mA} \\  I_{\text{out}}  \le 4.0 \text{ mA} \\  I_{\text{out}}  \le 5.2 \text{ mA}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_f = t_f = 6 \text{ ns}$ )

			Gu	aranteed Li	mit	
Symbol	Parameter	V <sub>CC</sub>	− 55 to 25°C	≤ 85°C	≤ 125°C	Unit
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	2.0 3.0 4.5 6.0	6 10 30 35	4.8 8.0 24 28	4 6 20 24	MHz
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Clock to Q or Q (Figures 1 and 4)	2.0 3.0 4.5 6.0	150 75 26 22	190 90 32 28	225 110 38 33	ns
t <sub>PHL</sub>	Maximum Propagation Delay, Reset to Q or $\overline{\mathbb{Q}}$ (Figures 2 and 4)	2.0 3.0 4.5 6.0	125 70 22 19	155 85 27 24	190 110 34 30	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C <sub>in</sub>	Maximum Input Capacitance	_	10	10	10	pF

#### NOTES:

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Flip-Flop)*	35	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ . For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

For propagation delays with loads other than 50 pF, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).
 Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# **TIMING REQUIREMENTS** (Input $t_r = t_f = 6 \text{ ns}$ )

			Gu	aranteed Li	mit	
Symbol	Parameter	v <sub>cc</sub>	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
t <sub>su</sub>	Minimum Setup Time, Data to Clock (Figure 3)	2.0 3.0 4.5 6.0	100 45 20 17	125 65 25 21	150 85 30 26	ns
t <sub>h</sub>	Minimum Hold Time, Clock to Data (Figure 3)	2.0 3.0 4.5 6.0	5 3 3 3	5 3 3 3	5 3 3 3	ns
t <sub>rec</sub>	Minimum Recovery Time, Reset Inactive to Clock (Figure 2)	2.0 3.0 4.5 6.0	100 45 20 17	125 65 25 21	150 85 30 26	ns
t <sub>w</sub>	Minimum Pulse Width, Clock (Figure 1)	2.0 3.0 4.5 6.0	80 45 16 14	100 65 20 17	120 85 24 20	ns
t <sub>w</sub>	Minimum Pulse Width, Reset (Figure 2)	2.0 3.0 4.5 6.0	80 45 16 14	100 65 20 17	120 85 24 20	ns
t <sub>r</sub> , t <sub>f</sub>	Maximum Input Rise and Fall Times (Figure 1)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# **SWITCHING WAVEFORMS**

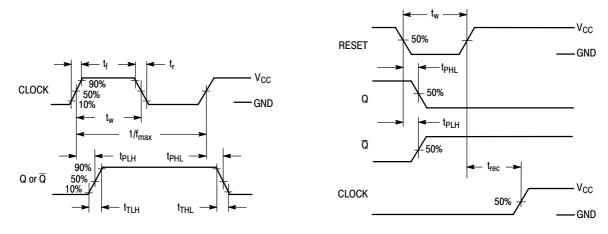
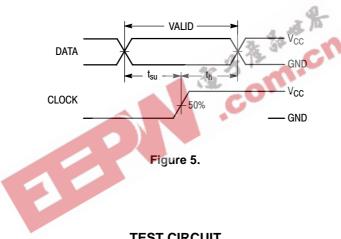
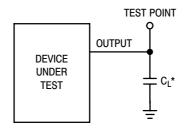


Figure 3.

Figure 4.



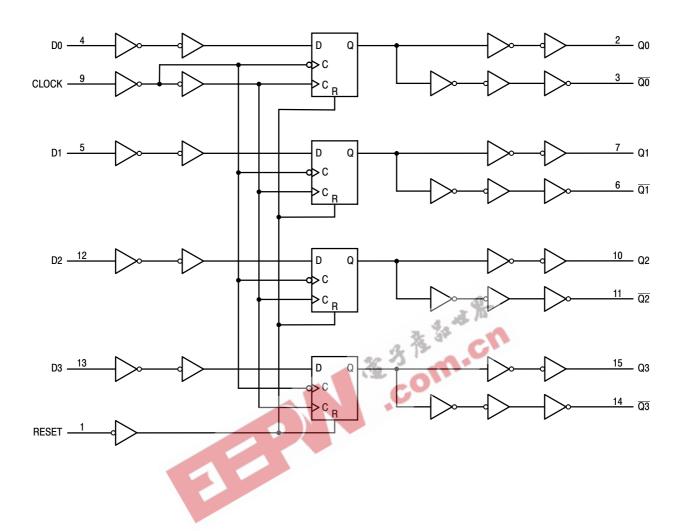
# **TEST CIRCUIT**



\*Includes all probe and jig capacitance

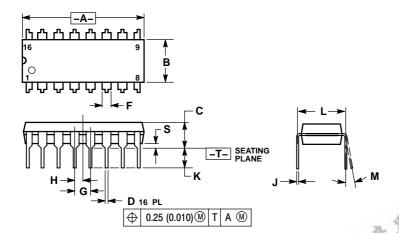
Figure 6.

# **EXPANDED LOGIC DIAGRAM**



# **PACKAGE DIMENSIONS**

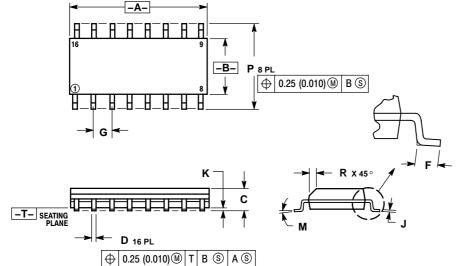
PDIP-16 **N SUFFIX** CASE 648-08 **ISSUE T** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOULD BLASUL.
- MOLD FLASH.
  5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100	BSC	2.54	BSC
Н	0.050	BSC	1.27	BSC
mJ	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
110	0.295	0.305	7.50	7.74
M	_ 0°	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01





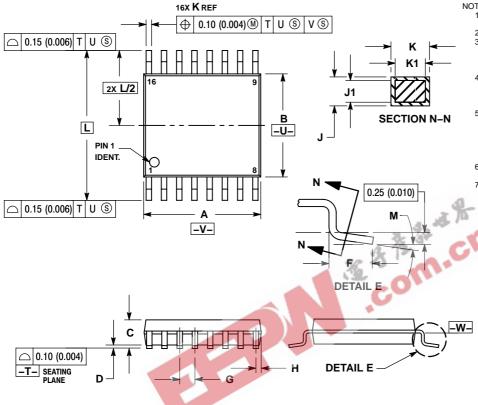
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

- CONTROLLING DIMENSION: MILLIMETER.
   DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
   MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
   DIMENSION D DOES NOT INCLUDE DAMBAR.
- PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL
  IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

# **PACKAGE DIMENSIONS**

TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE A** 



#### NOTES:

- OTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

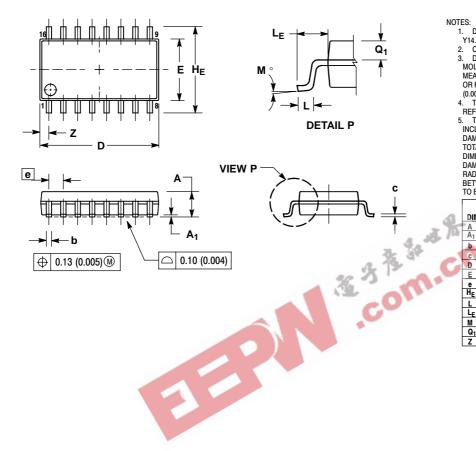
  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. SHALL NOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
Г	6.40	BSC	0.252 BSC		
М	0 °	8°	0°	8°	

#### PACKAGE DIMENSIONS

SOEIAJ-16 **F SUFFIX** CASE 966-01 **ISSUE O** 



#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER. B. DIMENSIONS D AND E DO NOT INCLUDE
  MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- (0.000) PEH SIDE.

  TERMINAL NUMBERS ARE SHOWN FOR
  REFERENCE ONLY.

  THE LEAD WIDTH DIMENSION (b) DOES NOT
  INCLUDE DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
  DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 ( 0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D T	9.90	10.50	0.390	0.413
Ε	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z		0.78		0.031

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